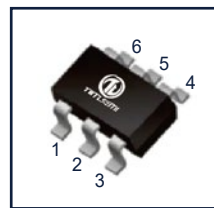
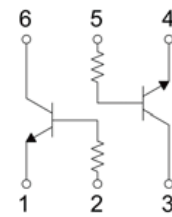


Features

- Two DTC143T chips in a package
- Transistor elements are independent, eliminating interference
- Mounting cost and area can be cut in half



SOT-363



Equivalent Circuit

Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	50	V
V_{CE0}	Collector-Emitter Voltage	50	V
V_{EB0}	Emitter-Base Voltage	5	V
I_C	Collector Current	100	mA
P_C	Collector Power Dissipation	150	mW
T_J, T_{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

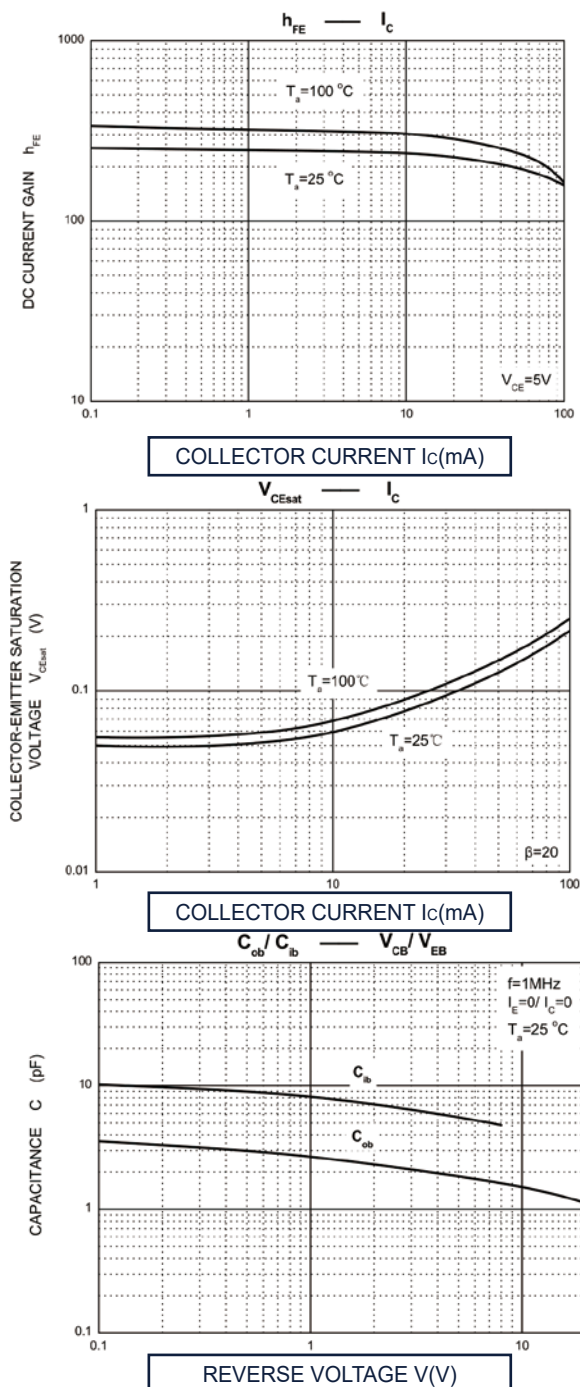
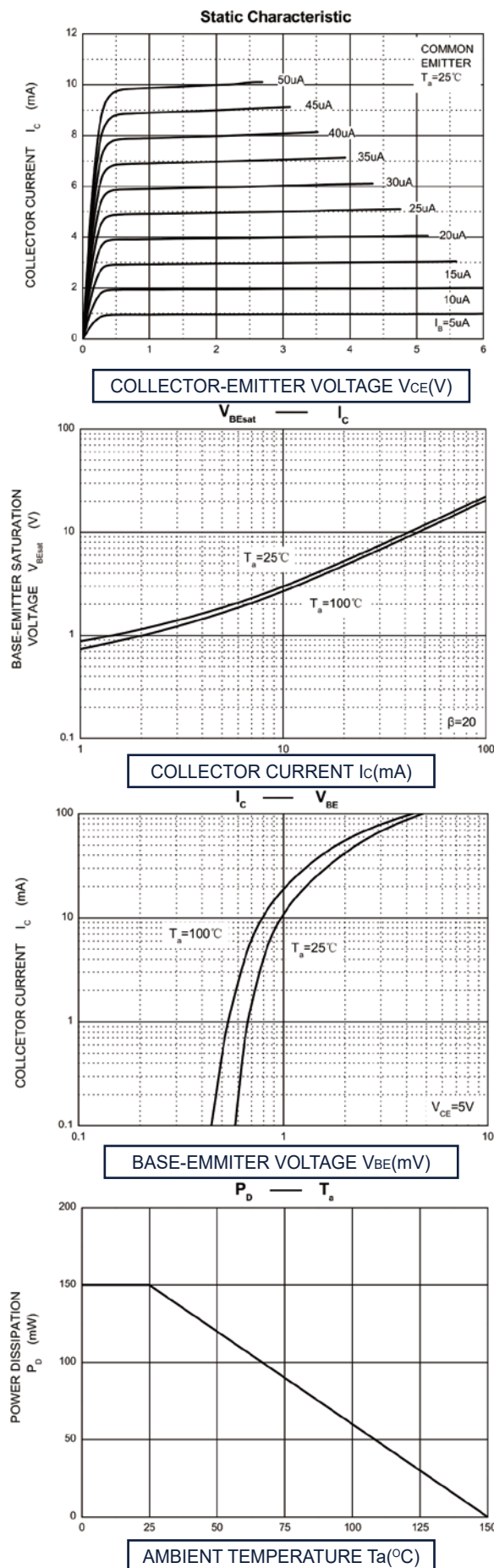
Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)CB0}$	Collector-base breakdown voltage	$I_C=50\mu\text{A}$	50			V
$V_{(BR)CE0}$	Collector-emitter breakdown voltage	$I_C=1\text{mA}$	50			V
$V_{(BR)EB0}$	Emitter-base breakdown voltage	$I_E=50\mu\text{A}$	5			V
I_{CB0}	Collector cut-off current	$V_{CB}=50\text{V}$			0.5	μA
I_{EB0}	Emitter cut-off current	$V_{EB}=4\text{V}$			0.5	μA
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=5\text{mA}, I_B=0.25\text{mA}$			0.3	V
h_{FE}	DC current gain	$V_{CE}=5\text{V}, I_C=1\text{mA}$	100		600	
R_1	Input resistance		3.29	4.7	6.11	$\text{K}\Omega$
f_T	Transition frequency	$V_{CE}=10\text{V}, I_E=-5\text{mA}, f=100\text{MHz}$		250		MHz

Ordering information

Product ID	Pack	Naming rule	Marking	Qty(PCS)
UMH3N	SOT-363	UMH3N 产品名称 product name	H3	3000

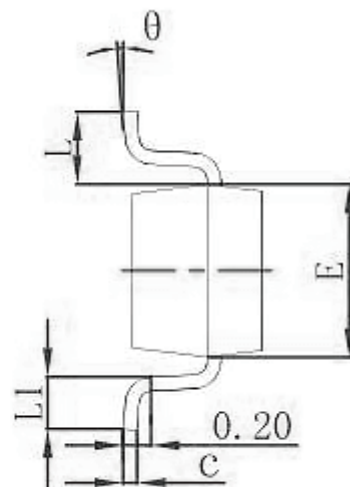
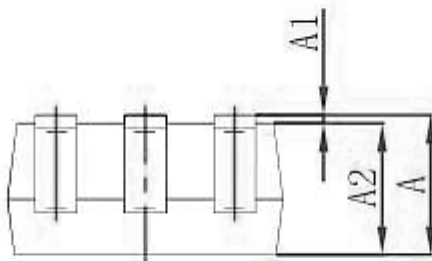
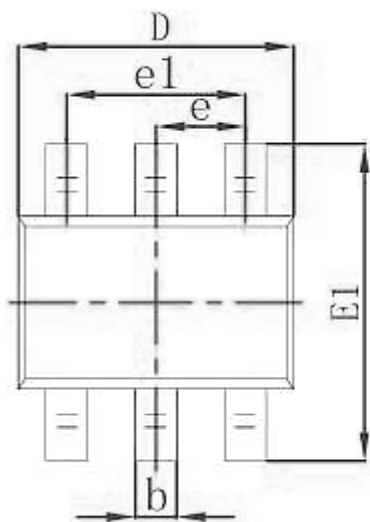


Typical Characteristics





SOT-363 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°